

Inventor: Brian A. Vaartstra

Title: Methods of Forming a Phosphorus Doped Silicon Dioxide
Comprising Layer, and a Method of Forming Trench Isolation in the
Fabrication of Integrated Circuitry

Assignee: Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
37 CFR § 1.56. Copies of the cited art are included. No admission is made
regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 7-7-03

Attorney: 

Mark S. Matkin
Reg. No. 32,268

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-2308SERIAL NO.
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(Use several sheets if necessary)

APPLICANT: Brian A. Vaartstra

FILING DATE
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Unknown

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,300,219 B1	10/09/01	Doan et al.			
	AB	6,534,395 B2	03/18/03	Werkhoven et al.			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ	02/27063 A2	04.04.02	WIPO (Gordon et al.)				
	AK							
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AM	Hausmann et al., <i>Rapid Vapor Deposition of Highly Conformal Silica Nanolaminates</i> , 298 SCIENCE 402-406, (11 October 2002).
	AN	Klaus et al., <i>Atomic Layer Deposition of SiO₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions</i> , 6 SURFACE REVIEW AND LETTERS, Nos. 3 & 4, pp. 435-448 (1999).
	AO	Miller et al., <i>Self-limiting chemical vapor deposition of an ultra-thin silicon oxide film using tri-(tert-butoxy)silanol</i> , 397 THIN SOLID FILMS 78-82 (2001).
EXAMINER		DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.